

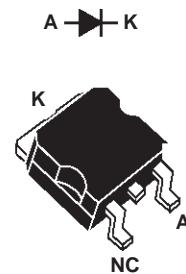
HIGH EFFICIENCY FAST RECOVERY DIODES

MAIN PRODUCT CHARACTERISTICS

$I_{F(AV)}$	8 A
V_{RRM}	200 V
trr	35 ns
V_F	0.85 V

FEATURES AND BENEFITS

- VERY SMALL CONDUCTION LOSSES
- NEGLIGIBLE SWITCHING LOSSES
- LOW FORWARD AND REVERSE RECOVERY TIMES
- HIGH SURGE CURRENT
- SMD



D²PAK
(Plastic)

DESCRIPTION

Single rectifier suited for switchmode power supply and high frequency DC to DC converters. Packaged in a surface mount package D²PAK, this device is intended for use in high frequency inverters, free wheeling and polarity protection applications.

ABSOLUTE MAXIMUM RATINGS

Symbol	Parameter	Value	Unit
V_{RRM}	Repetitive peak reverse voltage	200	V
$I_{F(RMS)}$	RMS forward current	16	A
$I_{F(AV)}$	Average forward current	8	A
I_{FSM}	Surge non repetitive forward current (All pins connected)	80	A
I_{FRM}	Repetitive peak forward current	75	A
T_{stg} T_j	Storage and junction temperature range	- 40 to + 150	°C

BYW29G-200

THERMAL RESISTANCE

Symbol	Parameter	Value	Unit
R _{th} (j-c)	Junction to case thermal resistance	2.8	°C/W

STATIC ELECTRICAL CHARACTERISTICS

Symbol	Parameter	Test Conditions		Min.	Typ.	Max.	Unit
I _R *	Reverse leakage current	V _R = V _{RRM}	T _j = 25°C			10	μA
			T _j = 100°C			0.6	mA
V _F **	Forward voltage drop	I _F = 5 A	T _j = 125°C			0.85	V
		I _F = 10 A	T _j = 125°C			1.05	
		I _F = 10 A	T _j = 25°C			1.15	

Pulse test : * tp = 5 ms, duty cycle < 2 %

** tp = 380 μs, duty cycle < 2 %

To evaluate the conduction losses use the following equation :

$$P = 0.65 \times I_{F(AV)} + 0.040 I_{F^2(RMS)}$$

RECOVERY CHARACTERISTICS

Symbol	Parameter	Test Conditions		Min.	Typ.	Max.	Unit
t _{rr}	Reverse recovery time	T _j = 25°C I _{rr} = 0.25 A	I _F = 0.5A I _R = 1A			25	ns
		T _j = 25°C dI _F /dt = -50A/μs	I _F = 1A V _R = 30V			35	
t _{fr}	Forward recovery time	T _j = 25°C dI _F /dt = 100A/μs V _{FR} = 1.1 x V _F max	I _F = 1A		15		ns
V _{FP}	Peak forward voltage	T _j = 25°C dI _F /dt = 100A/μs	I _F = 1A		2		V

PIN OUT configuration in D²PAK:



Fig.1 : Average forward power dissipation versus average forward current.

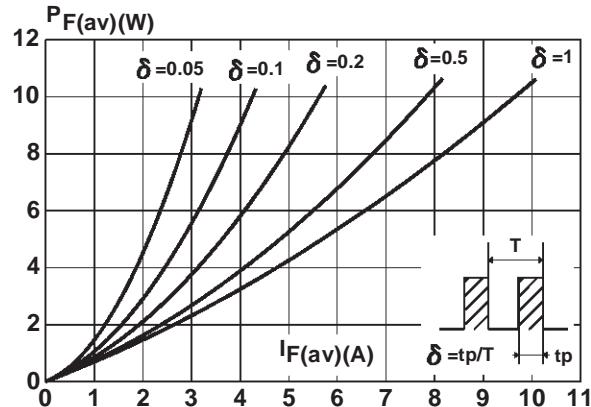


Fig.3 : Forward voltage drop versus forward current (maximum values).

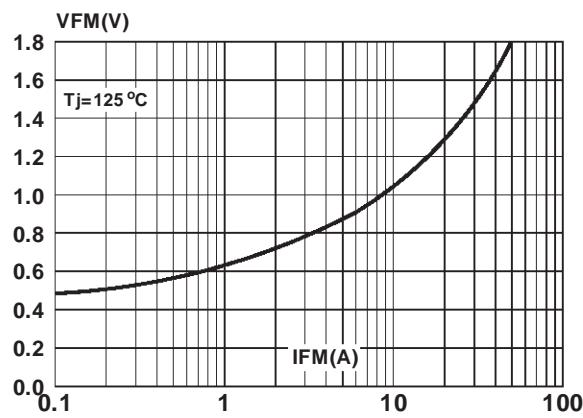


Fig.5 : Non repetitive surge peak forward current versus overload duration.

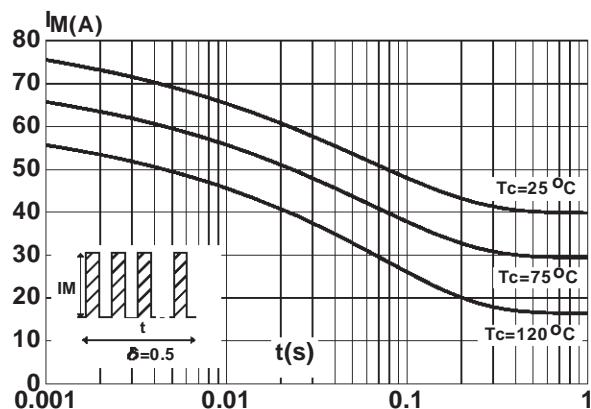


Fig.2 : Peak current versus form factor.

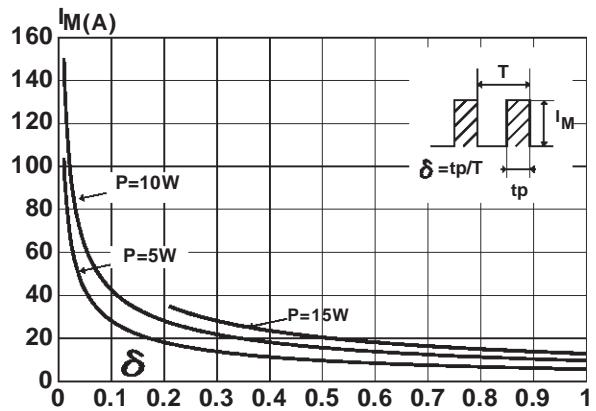


Fig.4 : Relative variation of thermal impedance junction to case versus pulse duration.

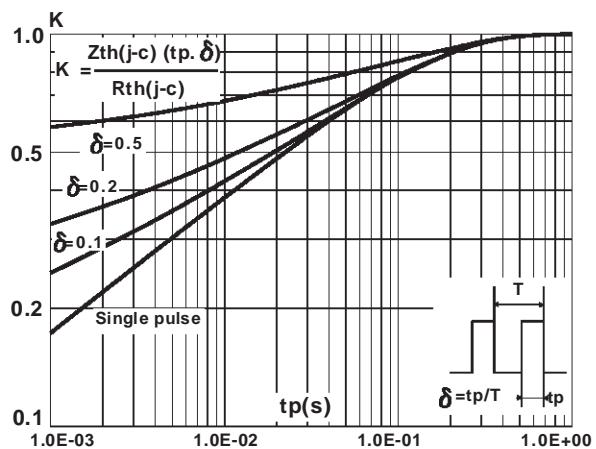
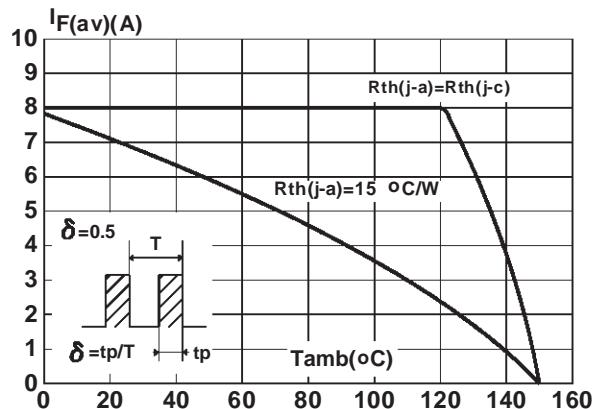


Fig.6 : Average current versus ambient temperature. (duty cycle : 0.5)



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Fig.7 : Junction capacitance versus reverse voltage applied (Typical values).

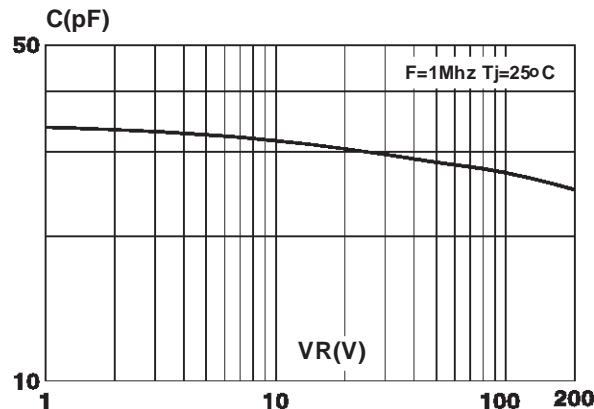


Fig.9 : Peak reverse current versus dIF/dt.

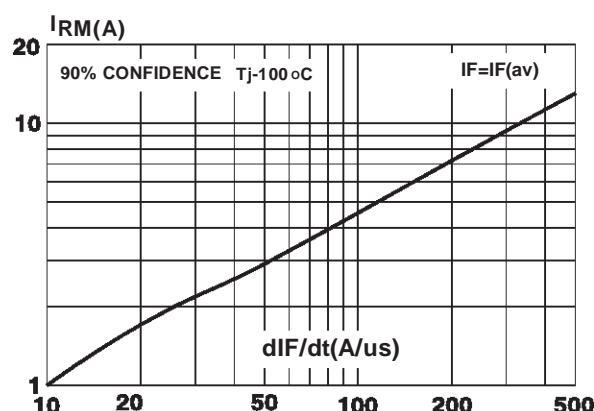


Fig.8 : Recovery charges versus dIF/dt.

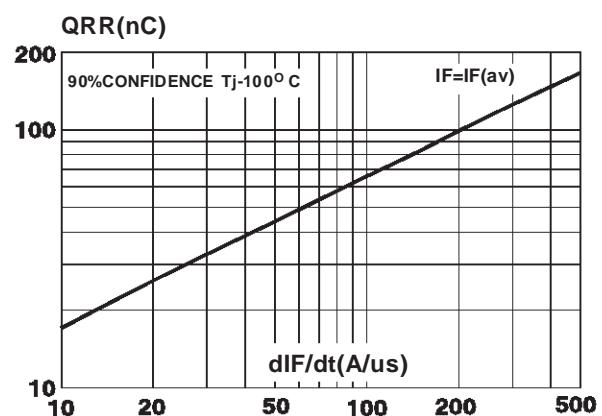
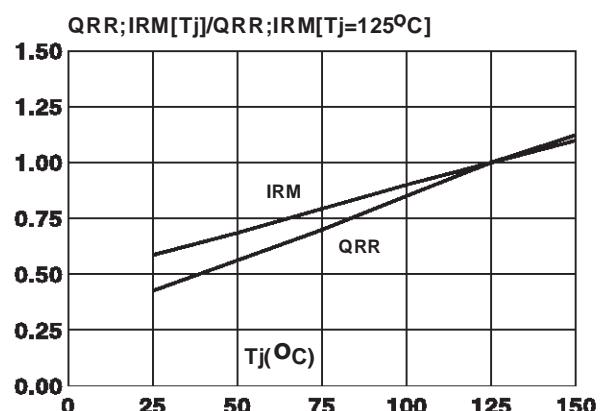
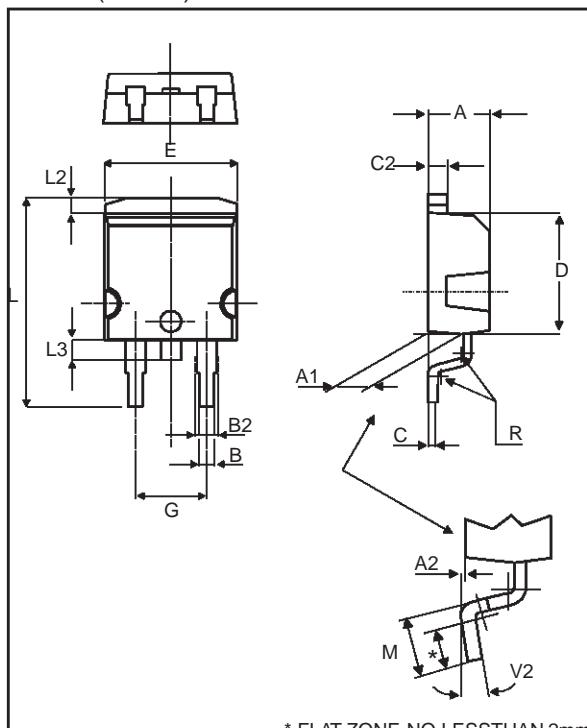
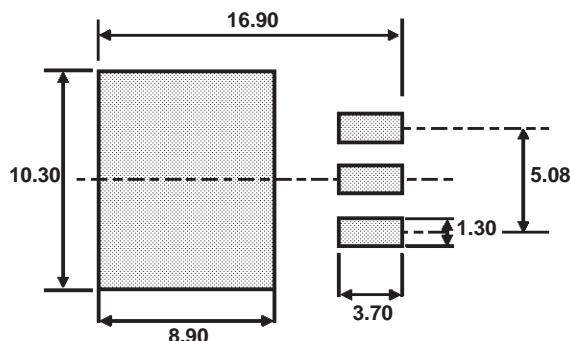


Fig.10 : Dynamic parameters versus junction temperature.



PACKAGE MECHANICAL DATA
D²PAK (Plastic)


REF.	DIMENSIONS			
	Millimeters		Inches	
	Min.	Max.	Min.	Max.
A	4.40	4.60	0.173	0.181
A1	2.49	2.69	0.098	0.106
A2	0.03	0.23	0.001	0.009
B	0.70	0.93	0.027	0.037
B2	1.14	1.70	0.045	0.067
C	0.45	0.60	0.017	0.024
C2	1.23	1.36	0.048	0.054
D	8.95	9.35	0.352	0.368
E	10.00	10.40	0.393	0.409
G	4.88	5.28	0.192	0.208
L	15.00	15.85	0.590	0.624
L2	1.27	1.40	0.050	0.055
L3	1.40	1.75	0.055	0.069
M	2.40	3.20	0.094	0.126
R	0.40 typ.		0.016 typ.	
V2	0°	8°	0°	8°

FOOT PRINT (in millimeters)

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